

ABSTRACT OF THE DISCLOSURE

Provided is a semiconductor device and a method of fabricating the semiconductor device, in which electric characteristics of a gate insulating film thereof in the vicinity of an element isolation region are equal to electric characteristics of the gate insulating film at portions other than the vicinity of the element isolation region. A semiconductor device of the present invention includes a semiconductor substrate, shallow trench isolation regions formed in the semiconductor substrate, source and drain regions formed in the semiconductor substrate, the source and drain regions sandwiching a surface of the semiconductor substrate to define a channel, gate insulating films having equal thicknesses in a central portion of the channel and in portions contacting with on the shallow trench isolation regions, and gate electrodes formed on the gate insulating films.